

APPLICATION DATA SHEET

Electronic Version v14

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Applicant Information:

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Customer Number:	29453	*29453*
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Application Information:

Title of Invention:	III Nitride Single Crystal, and Manufacturing Method Therefor and Semiconductor Device Therewith
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Application Type: regular, utility

Attorney Docket Number: 39.070

Botanic Information:

Publication Information:

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Representative Information:

practitioner(s) at Customer Number:

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as my attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.

Domestic Priority Information:

Foreign Priority Information:

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